

LEI Mercury Probe

汞探针测试

LEI Model 2017B, could measure carrier concentration distribution, such as GaN, SiC etc. using Mercury Probe method

LEI Model 2017B, 通过汞探针接触方法, 对各类半导体材料的载流子浓度分布进行测试, 特别适合GaN, SiC等化合物材料。

Capability:

- Multiple Schottky available 可提供多个肖特基结构
- Minimal series resistance via innovative Schottky/return dot 特殊设计的肖特基接触, 使串联电阻最小
- Precision vacuum control 精确的真空控制



Model 2017B